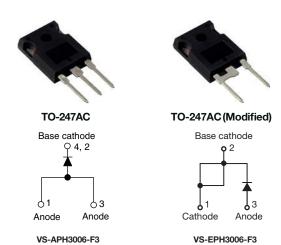


Vishay Semiconductors

Hyperfast Rectifier, 30 A FRED Pt®



PRODUCT SUMMARY				
Package	TO-247AC, TO-247AC modified			
I _{F(AV)}	30 A			
V_{R}	600 V			
V _F at I _F	2.65 V			
t _{rr} (typ.)	27 ns			
T _J max.	175 °C			
Diode variation	Single die			

FEATURES

- Low forward voltage drop
- Hyperfast soft recovery time
- 175 °C operating junction temperature
- Compliant to RoHS Directive 2002/95/EC
- Designed and qualified according to JEDEC-JESD47





RoHS COMPLIANT

DESCRIPTION/APPLICATIONS

Hyperfast recovery rectifiers designed with optimized performance of forward voltage drop, hyperfast recovery time, and soft recovery.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in PFC Boost stage in the AC/DC section of SMPS, inverters or as freewheeling diodes.

The extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

ABSOLUTE MAXIMUM RATINGS					
PARAMETER	SYMBOL	TEST CONDITIONS	MAX.	UNITS	
Repetitive peak reverse voltage	V _{RRM}		600	V	
Average rectified forward current	I _{F(AV)}	T _C = 112 °C	30	^	
Non-repetitive peak surge current	I _{FSM}	T _C = 25 °C	180	A	
Operating junction and storage temperatures	T _J , T _{Stg}		- 65 to 175	°C	

ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Breakdown voltage, blocking voltage	V _{BR} , V _R	Ι _R = 100 μΑ	600	-	-	
Forward voltage	V _E	I _F = 30 A	-	2.0	2.65	V
Torward voltage	VF	I _F = 30 A, T _J = 150 °C	-	1.4	1.8	
Poveree leekage current		$V_R = V_R$ rated	-	-	30	uА
Reverse leakage current I _R		$T_J = 150 ^{\circ}\text{C}, V_R = V_R \text{ rated}$	-	-	300	μΑ
Junction capacitance	C _T	V _R = 600 V	-	20	-	pF
Series inductance	L _S	Measured lead to lead 5 mm from package body	-	8.0	-	nΗ

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Vishay Semiconductors Hyperfast Rectifier, 30 A FRED Pt®



DYNAMIC RECOVERY CHARACTERISTICS (T _J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CO	NDITIONS	MIN.	TYP.	MAX.	UNITS
		$I_F = 1 A, dI_F/dt = 5$	0 A/μs, V _R = 30 V	-	26	35	
Reverse recovery time	t _{rr}	T _J = 25 °C	$I_F = 30 \text{ A}$ $dI_F/dt = 200 \text{ A/}\mu\text{s}$ $V_R = 200 \text{ V}$	-	26	-	ns
		T _J = 125 °C		-	70	-	
Dools recovery assuremt		T _J = 25 °C		-	3.5	-	Α
Peak recovery current	IRRM	T _J = 125 °C		-	7.6	-	^
Reverse recovery charge Q _{rr}	0	T _J = 25 °C		-	50	-	~ C
	Q _{rr}	T _J = 125 °C		-	280	-	nC

THERMAL - MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Maximum junction and storage temperature range	T _J , T _{Stg}		- 65	-	175	°C
Thermal resistance, junction to case	R _{thJC}		-	0.7	1.1	°C/W
Thermal resistance, junction to ambient per leg	R _{thJA}	A Typical socket mount		-	70	
Thermal resistance, case to heatsink	R _{thCS}	Mounting surface, flat, smooth and greased	-	0.5	-	
Weight			-	5.5	-	g
Weight			-	0.2	-	oz.
Mounting torque			1.2 (10)	-	2.4 (20)	kgf · cm (lbf · in)
Marking device		Case style TO-247AC	APH3006			
Marking device		Case style TO-247AC modified		EPH	3006	



Hyperfast Rectifier, 30 A FRED Pt® Vishay Semiconductors

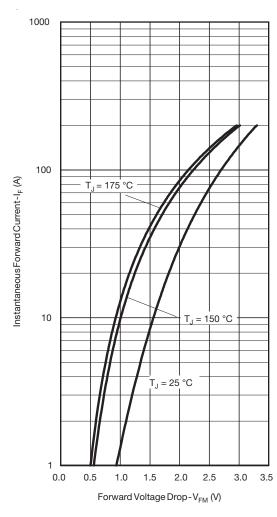


Fig. 1 - Typical Forward Voltage Drop Characteristics

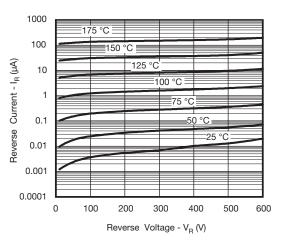


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

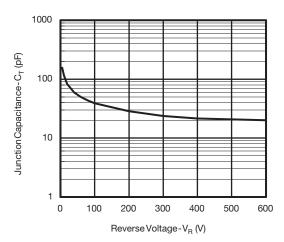


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

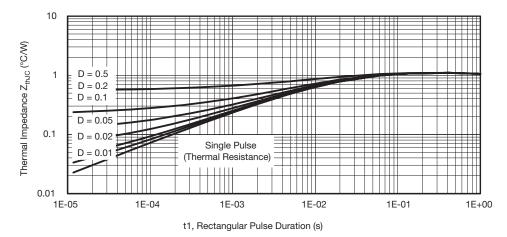


Fig. 4 - Max. Thermal Impedance Z_{thJC} Characteristics

Vishay Semiconductors Hyperfast Rectifier, 30 A FRED Pt®



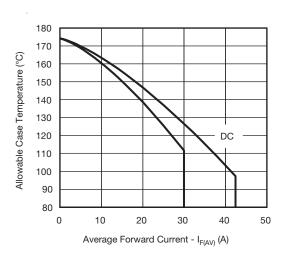


Fig. 5 - Maximum Allowable Case Temperature vs. Average Forward Current

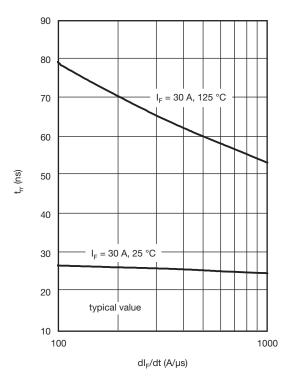


Fig. 7 - Typical Reverse Recovery vs. dl_F/dt

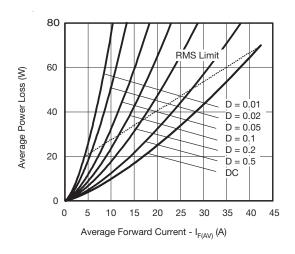


Fig. 6 - Forward Power Loss Characteristics

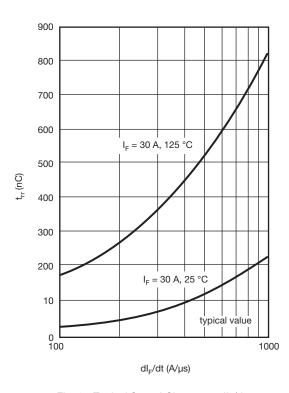


Fig. 8 - Typical Stored Charge vs. dl_F/dt



Hyperfast Rectifier, 30 A FRED Pt® Vishay Semiconductors

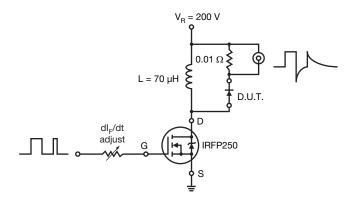
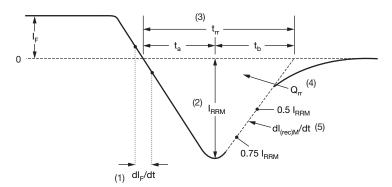


Fig. 9 - Reverse Recovery Parameter Test Circuit



- (1) dl_F/dt rate of change of current through zero crossing
- (2) I_{RRM} peak reverse recovery current
- (3) t_{rr} reverse recovery time measured from zero crossing point of negative going I_F to point where a line passing through 0.75 $\rm I_{RRM}$ and 0.50 $\rm I_{RRM}$ extrapolated to zero current.
- (4) Q_{rr} area under curve defined by t_{rr} and I_{RRM}

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(5) $dI_{(rec)M}/dt$ - peak rate of change of current during t_b portion of t_{rr}

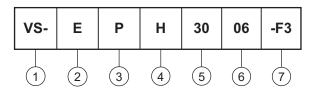
Fig. 10 - Reverse Recovery Waveform and Definitions

Vishay Semiconductors Hyperfast Rectifier, 30 A FRED Pt®



ORDERING INFORMATION TABLE

Device code



Vishay Semiconductors product

Ultrafast MUR series

• A = Single diode

• E = Single diode (modified)

P = TO-247AC

H = Hyperfast recovery time

Current code (30 = 30 A)

Voltage code (06 = 600 V)

F3 = RoHS compliant and totally lead (Pb)-free

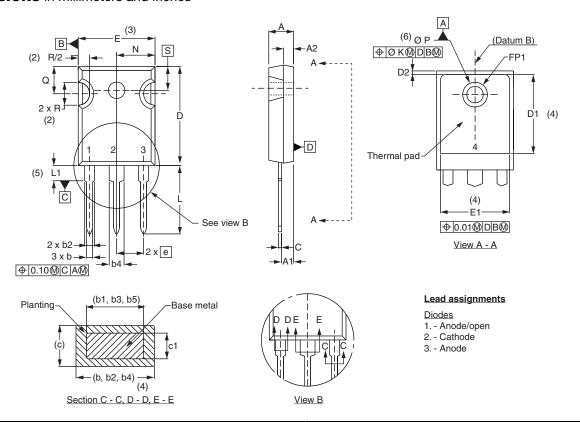
ORDERING INFORMATION (Example)					
PREFERRED P/N	QUANTITY PER TUBE	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION		
VS-APH3006-F3	25	500	Antistatic plastic tube		
VS-EPH3006-F3	25	500	Antistatic plastic tube		

LINKS TO RELATED DOCUMENTS			
Dimensions	TO-247AC	www.vishay.com/doc?95223	
Difficusions	TO-247AC modified	www.vishay.com/doc?95253	
Dort moding information	TO-247AC	www.vishay.com/doc?95007	
Part marking information	TO-247AC modified	www.vishay.com/doc?95442	



Vishay Semiconductors

DIMENSIONS in millimeters and inches



SYMBOL	MILLIMETERS		INC	HES	NOTES
STIVIDUL	MIN.	MAX.	MIN.	MAX.	NOTES
Α	4.65	5.31	0.183	0.209	
A1	2.21	2.59	0.087	0.102	
A2	1.50	2.49	0.059	0.098	
b	0.99	1.40	0.039	0.055	
b1	0.99	1.35	0.039	0.053	
b2	1.65	2.39	0.065	0.094	
b3	1.65	2.37	0.065	0.094	
b4	2.59	3.43	0.102	0.135	
b5	2.59	3.38	0.102	0.133	
С	0.38	0.86	0.015	0.034	
c1	0.38	0.76	0.015	0.030	
D	19.71	20.70	0.776	0.815	3
D1	13.08	-	0.515	-	4

SYMBOL	MILLIMETERS		INC	HES	NOTES
STWIBOL	MIN.	MAX.	MIN.	MAX.	NOTES
D2	0.51	1.30	0.020	0.051	
E	15.29	15.87	0.602	0.625	3
E1	13.72	-	0.540	-	
е	5.46	BSC	0.215	BSC	
FK	2.	54	0.0	10	
L	14.20	16.10	0.559	0.634	
L1	3.71	4.29	0.146	0.169	
N	7.62	BSC	0	.3	
ΦР	3.56	3.66	0.14	0.144	
ФР1	1	6.98	-	0.275	
Q	5.31	5.69	0.209	0.224	
R	4.52	5.49	1.78	0.216	
S	5.51	BSC	0.217	BSC	

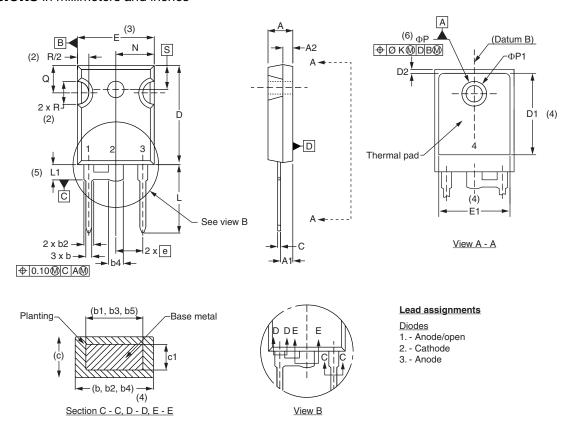
Notes

- (1) Dimensioning and tolerancing per ASME Y14.5M-1994
- (2) Contour of slot optional
- (3) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (4) Thermal pad contour optional with dimensions D1 and E1
- (5) Lead finish uncontrolled in L1
- (6) Ø P to have a maximum draft angle of 1.5 to the top of the part with a maximum hole diameter of 3.91 mm (0.154")
- (7) Outline conforms to JEDEC outline TO-247 with exception of dimension c



Vishay Semiconductors

DIMENSIONS in millimeters and inches



SYMBOL	MILLIMETERS		INC	HES	NOTES
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E1	13.72	-	0.540	1	
е	5.46	BSC	0.215	BSC	
ΦК	2.	54	0.0	10	
L	14.20	16.10	0.559	0.634	
L1	3.71	4.29	0.146	0.169	
Ν	7.62	BSC	0	.3	
ΦР	3.56	3.66	0.14	0.144	
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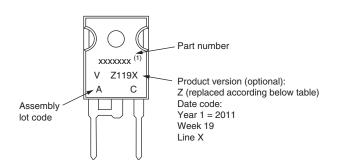
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Part Marking Information

Vishay Semiconductors

TO-247AC modified E



Example: This is a xxxxxxx (1) with assembly lot code AC,

assembly lot code AC, assembled on WW 19, 2011 in the assembly line "X"

Note

(1) If part number contain "H" as last digit, product is AEC-Q101 qualified

ENVIRONMENTAL NAMING CODE (Z)	PRODUCT DEFINITION
A	Termination lead (Pb)-free
В	Totally lead (Pb)-free
E	RoHS compliant and termination lead (Pb)-free
F	RoHS compliant and totally lead (Pb)-free
M	Halogen-free, RoHS compliant and termination lead (Pb)-free
N Halogen-free, RoHS compliant and totally lead (Pb)-free	
G Green	





Vishay

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